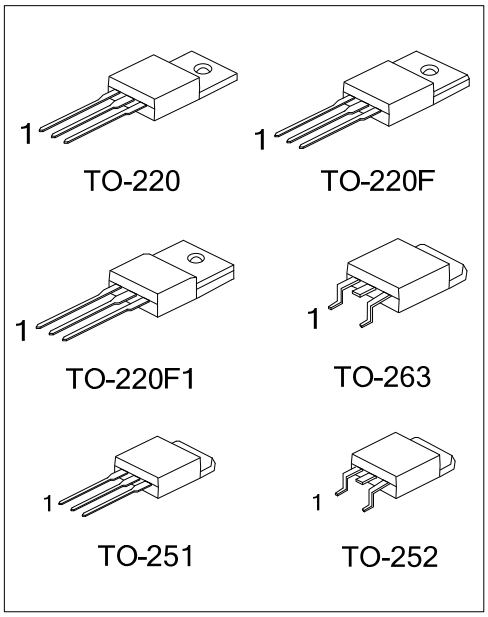
15NM60

Power MOSFET

15A, 600V N-CHANNEL SUPER-JUNCTION MOSFET



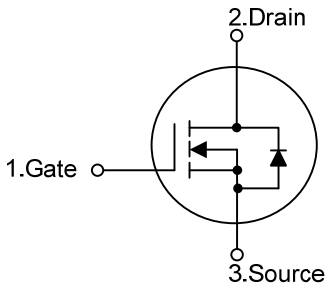
■ DESCRIPTION

The **UTC 15NM60** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

■ FEATURES

* $R_{DS(ON)}$ < 0.35Ω @ V_{GS}=10V, I_D=7.5A
* By using Super Junction Structure
* Fast Switching
* With 100% Avalanche Tested

■ SYMBOL



■ ORDERING INFORMATION

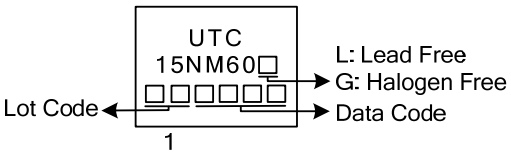
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
15NM60L-TA3-T	15NM60G-TA3-T	TO-220	G	D	S	Tube
15NM60L-TF3-T	15NM60G-TF3-T	TO-220F	G	D	S	Tube
15NM60L-TF1-T	15NM60G-TF1-T	TO-220F1	G	D	S	Tube
15NM60L-TM3-T	15NM60G-TM3-T	TO-251	G	D	S	Tube
15NM60L-TN3-R	15NM60G-TN3-R	TO-252	G	D	S	Tape Reel
15NM60L-TQ2-T	15NM60G-TQ2-T	TO-263	G	D	S	Tube
15NM60L-TQ2-R	15NM60G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

15NM60L-TA3-T
(1) Packing Type
(2) Package Type
(3) Green Package

(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F, TM3: TO-251, TN3: TO-252, TQ2: TO-263
(3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	15	A
	Pulsed (Note 2)	I_{DM}	60	A
Avalanche Current (Note 2)		I_{AR}	6.3	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	198	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220F/TO-220F1	P_D	38.5	W
	TO-220/TO-263		250	W
	TO-251/TO-252		85	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L=10mH, I_{AS}=6.3A, V_{DD}= 50V, R_G=25Ω, Starting T_J=25°C
4. I_{SD} ≤15A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J=25°C

■ THERMAL DATA

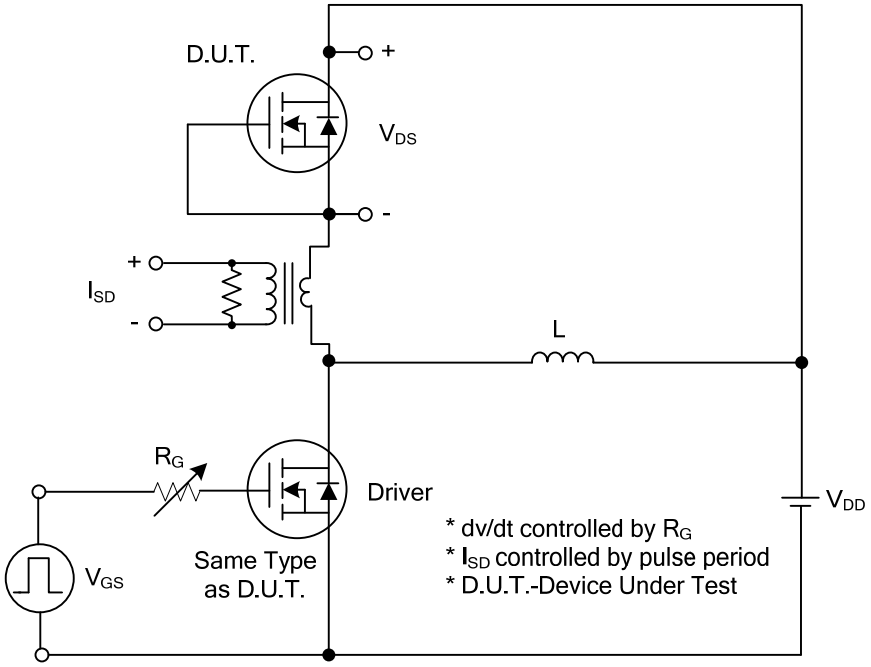
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-220F/TO-220F1	θ_{JC}	3.3	°C/W
	TO-220/TO-263		0.5	°C/W
	TO-251/TO-252		1.5	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

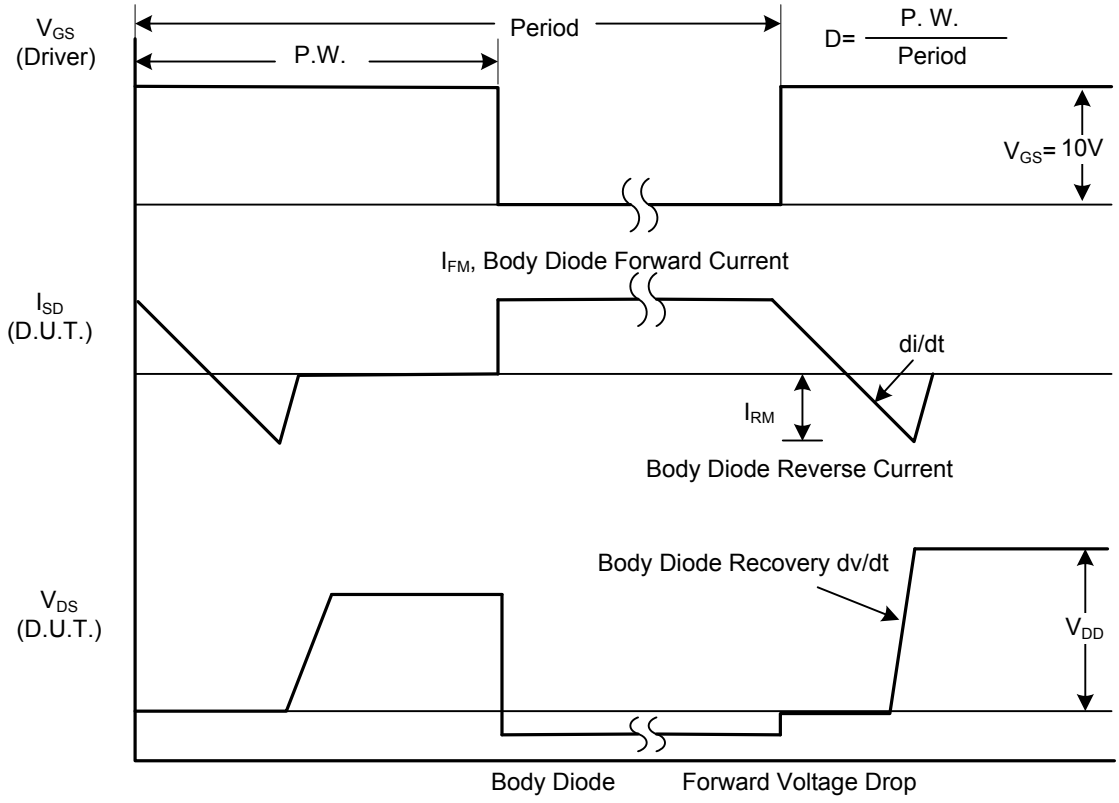
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	600			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=600V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{DS}=0V ,V_{GS}=30V			100	nA
	Reverse		V_{DS}=0V ,V_{GS}=-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}= V_{GS}, I_D=250μA	2.5		4.5	V
Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=7.5A			0.35	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		1140		pF
Output Capacitance		C_{OSS}			500		pF
Reverse Transfer Capacitance		C_{RSS}			18		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=50V, V_{GS}=10V, I_D=1.3A , I_G=100μA (Note 1, 2)		140		nC
Gate to Source Charge		Q_{GS}			10		nC
Gate to Drain Charge		Q_{GD}			25		nC
Turn-ON Delay Time (Note 1)		$t_{D(ON)}$	V_{DD}=30V, I_D=0.5A, R_G=25Ω V_{GS}=10V (Note 1, 2)		78		ns
Rise Time		t_R			140		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			262		ns
Fall-Time		t_F			132		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				15	A
Maximum Body-Diode Pulsed Current		I_{SM}				60	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S =15A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t_{rr}	I_S =15A, V_{GS}=0V, dI_F/dt=100A/μs				nS
Body Diode Reverse Recovery Charge		Q_{rr}					μC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

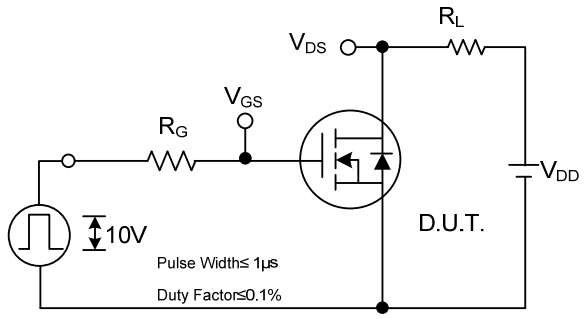


Peak Diode Recovery dv/dt Test Circuit

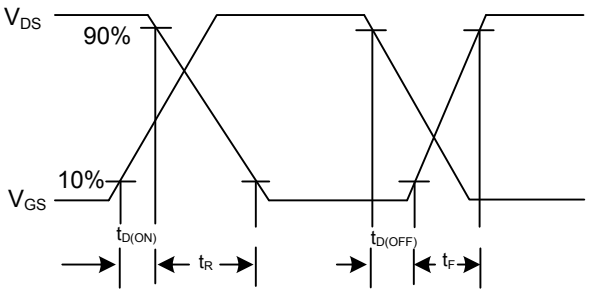


Peak Diode Recovery dv/dt Waveforms

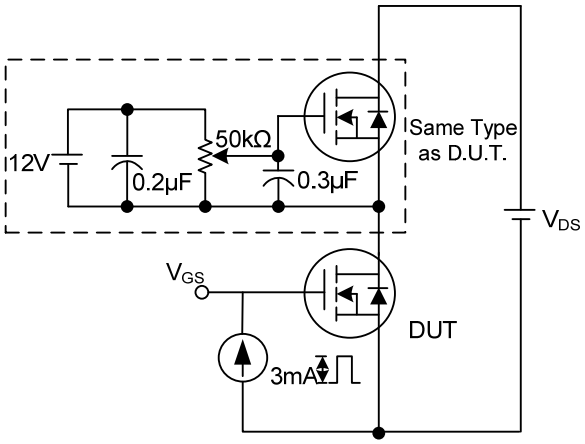
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



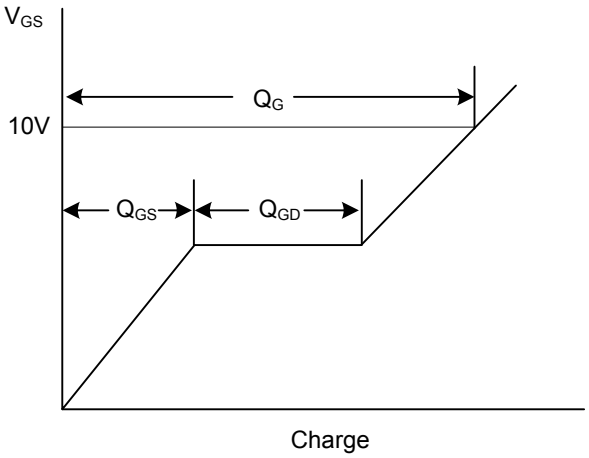
Switching Test Circuit



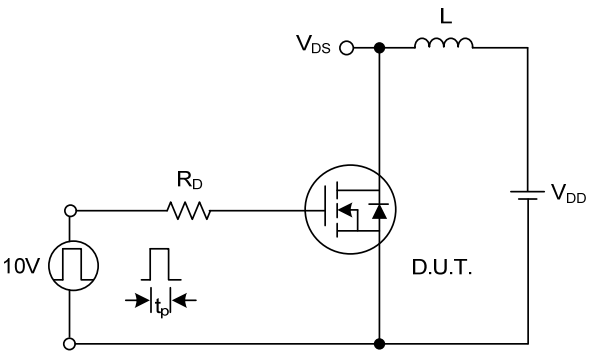
Switching Waveforms



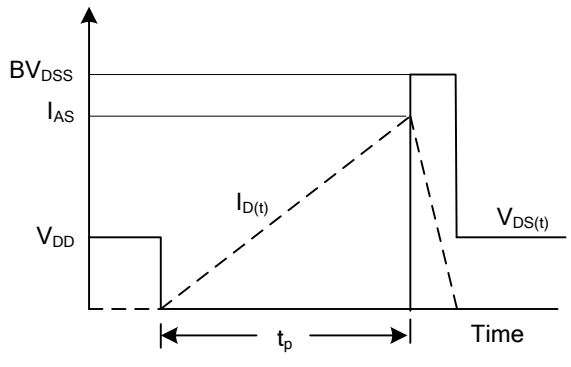
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms